| Session Code | [11] TuK3 |
|---|---|
| **Session Title** | Artificial Synapse Devices |
| **Date and Time** | Tuesday, October 5, 2021 / 15:40-16:40 |
| **Session Room** | Room K (402) |
| **Session Chair(s)** | Dohun Kim (Seoul Nat'l Univ., Korea) |

### [[11] TuK3-1] 15:40-15:55

Highly Li/Ag Intercalation-Based $MoTe_2$ Memory for Artificial Synapse Features

Woojong Yu and Gayoung Cho *(Sungkyunkwan Univ., Korea)*

### [[11] TuK3-2] 15:55-16:10

Sodium Beta-Alumina Based Charge Trap Flash Memory For Neuromorphic Application

Hae Won Cho, Pavan Pujar, Muhammad Naqi, Yong In Cho, and Sunkook Kim *(Sungkyunkwan Univ., Korea)*

### [[11] TuK3-3] 16:10-16:25

Dual Mode Operating Ferroelectric Floating Flash Memory for Synaptic Device using Van der Waals Materials

Sangyong Park *(Sungkyunkwan Univ., Korea)*, Seyong Oh *(Northwestern Univ., USA)*, Dongyoung Lee, and Jin-Hong Park *(Sungkyunkwan Univ., Korea)*

### [[11] TuK3-4] 16:25-16:40

Ferroelectric Polymer Based Brain Inspired Computing

Kim Sungjun, Park Jin-Hong *(Sungkyunkwan Univ., Korea)*, and Heo Keun *(Jeonbuk Nat'l Univ., Korea)*